

IN THE CLAIMS:

Claims 1-19 have been amended herein. All of the pending claims 1 through 19 are presented below. This listing of claims will replace all prior versions and listings in the application. Please enter these claims as amended.

1. (Currently Amended) A selective method for cleaning material from a wafer comprising:  
providing an ~~etchant-etchant~~-dispensing apparatus having an inlet thereto for an etchant agent and a tubular member having at least one thin annular edge thereon;  
placing an area of ~~said the~~ wafer within an annular member of ~~said the~~ ~~etchant-etchant~~-dispensing apparatus, ~~said at least one thin annular edge of said the~~ annular member of ~~said the~~ ~~etchant-etchant~~-dispensing apparatus located adjacent a portion of ~~said the~~ wafer;  
aligning ~~said the~~ wafer and ~~said the~~ ~~etchant-etchant~~-dispensing apparatus;  
dispensing an etchant onto ~~said at least one the~~ area of ~~said the~~ wafer ~~by using the said etchant~~ ~~etchant~~-dispensing apparatus; and  
removing ~~said the~~ etchant.

2. (Currently Amended) The method of claim 1, wherein ~~said~~-placing includes aligning ~~said the~~ wafer in a substantially perpendicular position in relation to ~~said the~~ ~~etchant~~ ~~etchant~~-dispensing apparatus.

3. (Currently Amended) The method of claim 1, wherein ~~said~~-aligning comprises aligning ~~said the~~ wafer to ~~said the~~ ~~etchant-etchant~~-dispensing apparatus.

4. (Currently Amended) The method of claim 1, wherein ~~said~~-aligning comprises aligning ~~said the~~ ~~etchant-etchant~~-dispensing apparatus to ~~said the~~ wafer.

5. (Currently Amended) The method of claim 1, wherein ~~said~~-aligning comprises aligning-~~said~~ the wafer substantially perpendicular to-~~said~~ the at least one thin annular edge of ~~said~~ the annular member of-~~said~~ the ~~etchant-etchant~~-dispensing apparatus.

6. (Currently Amended) The method of claim 1, wherein ~~said~~-aligning includes aligning-~~said~~ the at least one thin annular edge of-~~said~~ the annular member of-~~said~~ the ~~etchant etchant~~-dispensing apparatus substantially perpendicular to-~~said~~ a portion of-~~said~~ the wafer adjacent-~~said~~ at least one the area thereon.

7. (Currently Amended) The method of claim 1, wherein-~~said~~ the material includes at least one of chemical mechanical planarization process slurry material, a metal material, a photoresist material, a dielectric material, and a polysilicon material.

8. (Currently Amended) The method of claim 7, wherein-~~said~~ the metal material includes a refractory metal.

9. (Currently Amended) The method of claim 1, wherein ~~said~~-removing-~~said~~ the etchant includes removal of-~~said~~ the etchant by one of suction and vacuum.

10. (Currently Amended) The method of claim 1, further comprising cleaning a surface of-~~said~~ the wafer.

11. (Currently Amended) The method of claim 10, wherein ~~the~~-cleaning-~~said~~ the surface of the wafer includes:

cleaning-a the surface of-~~said~~ the wafer with a cleaning agent; and  
rinsing-~~said~~ the wafer in deionized water.

12. (Currently Amended) The method of claim 1, wherein ~~said~~ the etchant includes at least one of a liquid, a liquid vapor, a gas, ammonia, hydrogen fluoride, nitric acid, hydrogen peroxide, ammonium fluoride, and mixtures thereof.

13. (Currently Amended) A selective cleaning method for removing a material from a wafer for a semiconductor fabrication process, ~~said process~~ the method comprising:  
chemical mechanical planarizing ~~said~~ the wafer prior to ~~said removing of~~ said the material from ~~said~~ the wafer;  
providing an ~~etchant~~ etchant-dispensing apparatus having a tubular member, an annular member having at ~~last~~ least one thin annular edge thereon, and an inlet for etchant;  
aligning at least one area of ~~said~~ the wafer and at least a portion of ~~said~~ the ~~etchant~~ etchant-dispensing apparatus;  
dispensing ~~said~~ an etchant onto ~~said~~ the at least one area of ~~said~~ the wafer; and  
removing ~~said~~ the etchant using a portion of ~~said~~ the ~~etchant~~ etchant-dispensing apparatus.

14. (Currently Amended) The method of claim 13, wherein ~~said~~ aligning includes one of aligning a portion of ~~said~~ the wafer in a substantially perpendicular position in relation to ~~said~~ the ~~etchant~~ etchant-dispensing apparatus, aligning a portion of ~~said~~ the wafer to ~~said~~ the ~~etchant~~ etchant-dispensing apparatus, aligning ~~said~~ the ~~etchant~~ etchant-dispensing apparatus to ~~said~~ the wafer, and aligning ~~said~~ the wafer substantially perpendicular to ~~said~~ the at least one thin annular edge of ~~said~~ annular member of the ~~etchant~~ etchant-dispensing apparatus.

15. (Currently Amended) The ~~process~~ method of claim 13, wherein ~~said~~ the material includes at least one of chemical mechanical planarization process slurry material, a metal material, a photoresist material, a dielectric material, and a polysilicon material.

16. (Currently Amended) The ~~process~~ method of claim 15, wherein ~~said~~ the metal material includes a refractory metal.

17. (Currently Amended) The ~~process~~ method of claim 13, wherein ~~said~~ removing ~~said~~ the etchant includes removal of ~~said~~ the etchant by one of suction and vacuum.

18. (Currently Amended) The ~~process~~ method of claim 13, further comprising cleaning a surface of ~~said~~ the wafer.

19. (Currently Amended) The ~~process~~ method of claim 18, wherein ~~the step of~~ cleaning ~~said~~ a surface of the wafer includes:  
cleaning ~~said~~ the surface of the wafer with a cleaning agent; and  
rinsing ~~said~~ the wafer in deionized water.